

points) Consider the circuit shown below, consisting of a resistor (with resistance R) and three diodes. The voltage drop across the resistor is denoted as V_R , while the current through the resistor is denoted as I_R . Use the constant-voltage-drop model for the diodes (with $V_D = 0.7 \text{ V}$) to answer the following questions.

$$+20 \text{ V} \longrightarrow I_R$$

a) Find the value of VR.

solution:

Using the constant-voltage-drop model with $V_D = 0.7V$, we observe:

Thus: VR = 20V-2.1V = 17.9VA

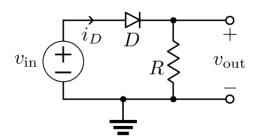
the value of R for which IR is equal to 2A.

solution: Writing Ohm's law for the resistor:

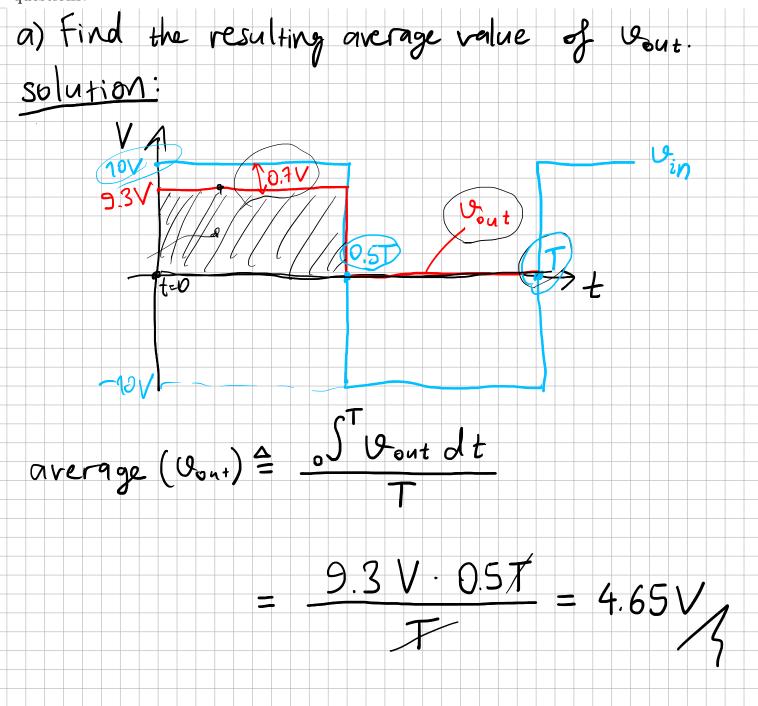
$$R = \frac{V_R}{I_R} = \frac{17.9 \text{ V}}{2 \text{ A}} = 8.95 \text{ SL}_4$$

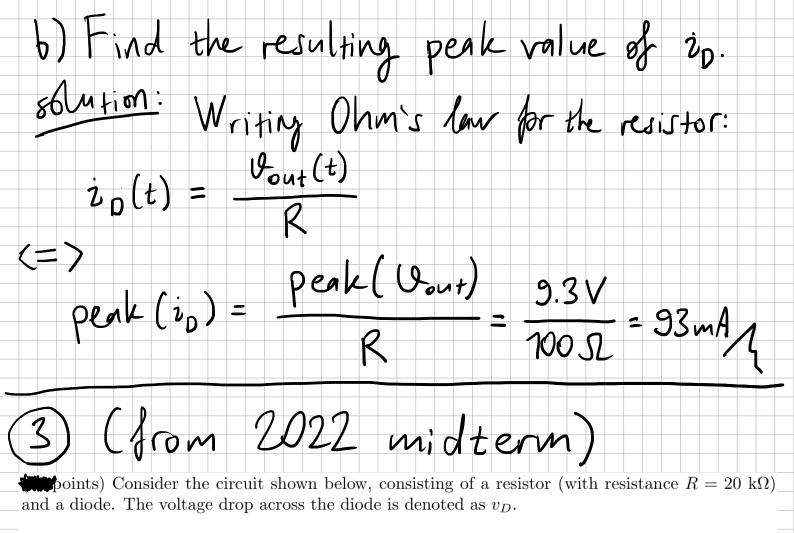
2) (from 2022 midtern)

points) Consider the circuit shown below, consisting of a resistor (with a resistance of R = 100 Ω) and a diode D. The input voltage is denoted as $v_{\rm in}$, while the diode current is denoted as i_D . The output voltage is the voltage drop across the resistor, and it is denoted as $v_{\rm out}$.



A symmetrical square wave of 10 V peak amplitude and zero average is applied to the circuit as $v_{\rm in}$. Use the constant-voltage-drop model for the diode (with $V_D=0.7$ V) to answer the following questions.





$$V^+$$
 $\stackrel{R}{\longrightarrow}$
 $\stackrel{V^+}{\longrightarrow}$
 $\stackrel{R}{\longrightarrow}$
 $\stackrel{D}{\longrightarrow}$

The power supply V^+ has a dc value of 20.7 V, and a 60-Hz sinusoid of 2-V peak amplitude superimposed on this dc value. Assume the diode to have a 0.7-V drop at 1-mA current and answer the following questions.

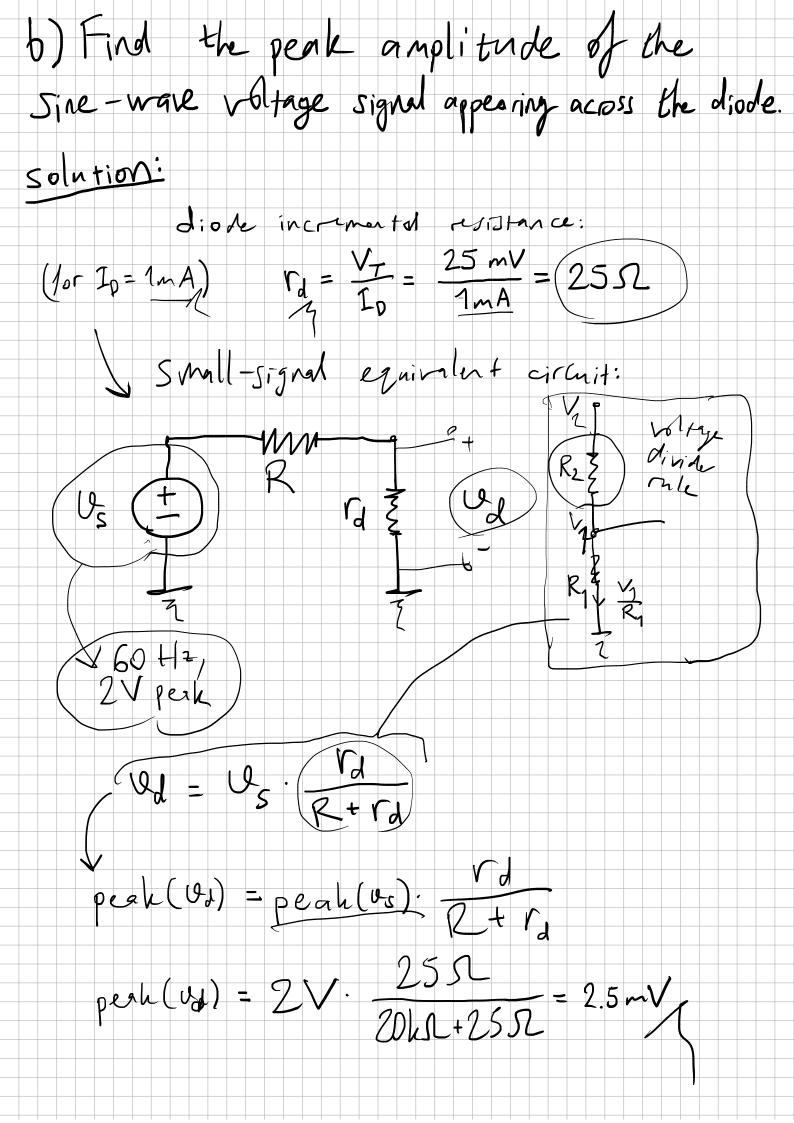
following questions.

Ca) Find the dc value of the diode current.

Solution:
$$V_{\Gamma}$$
 ting Ohm's law for the resistor:

 V_{Γ} ting Ohm's law for the resistor:

 V_{Γ} assume that this is $0.7V$
 V_{Γ} as $0.7V$
 V_{Γ



- points) Consider a MOSFET (n-channel enhancement-type) with the following parameters: W/L = 12, $t_{\rm ox} = 6$ nm, $\epsilon_{\rm ox} = 3.45 \times 10^{-11}$ F/m, $\mu_n = 450$ cm²/Vs, and $V_t = 0.7$ V.
- (a) (\bigcirc points) Find the value of V_{GS} (voltage between the gate and the source) needed to operate the MOSFET in the saturation region with a dc current of 120 μ A.
- (b) (points) Find the value of V_{OV} (overdrive voltage) required to make the MOSFET operate as a 2000- Ω resistor for very small v_{DS} (voltage between the drain and the source).

solution (a):

$$C_{\text{ox}} = \frac{\epsilon_{\text{ox}}}{t_{\text{ox}}} = \frac{3.45 \times 10^{-11} \text{ F/m}}{6 \times 10^{-9} \text{ m}} = 5.75 \times 10^{-3} \text{ F/m}^2$$
$$k'_n = \mu_n C_{\text{ox}} = \left(450 \text{ cm}^2/\text{Vs}\right) \times \left(5.75 \times 10^{-3} \text{ F/m}^2\right) = 258.75 \times 10^{-6} \text{ F/(Vs)}$$

For operation in the saturation region:

$$i_D = \frac{1}{2} k_n' \frac{W}{L} V_{OV}^2$$
$$120 \times 10^{-6} \text{ A} = \frac{1}{2} \times \left(258.75 \times 10^{-6} \text{ F/(V s)}\right) \times 12 \times V_{OV}^2$$
$$V_{OV} = 0.28 \text{ V}$$

$$V_{GS} = V_t + V_{OV} = 0.7 \text{ V} + 0.28 \text{ V} = 0.98 \text{ V}$$

solution (6):

For the MOSFET with v_{DS} very small

$$r_{DS} = \frac{1}{k_n' \frac{W}{L} V_{OV}}$$

2000
$$\Omega = \frac{1}{(258.75 \times 10^{-6} \text{ F/(V s)}) \times 12 \times V_{OV}}$$

$$V_{OV} = 0.16 \text{ V}$$

